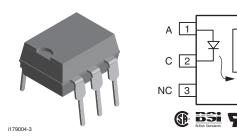




Optocoupler, Phototransistor Output, with Base Connection, 300 V BV_{CEO}

5 C

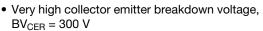


DESCRIPTION

The SFH640 is an optocoupler with very high BV_{CER} , a minimum of 300 V. It is intended for telecommunications applications or any DC application requiring a high blocking voltage.

FEATURES

- · Good CTR linearity with forward current
- Low CTR degradation





Isolation test voltage: 5300 V_{RMS}

Low coupling capacitance

- High common mode transient immunity
- Phototransistor optocoupler 6 pin DIP package with base connection
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- DIN EN 60747-5-2 (VDE 0884) available with option 1
- CSA 93751
- BSI IEC 60950; IEC 60065

ORDERING INFORMATION								
S F H 6 4 PART NUMBER	O - # X O # # T T CTR PACKAGE OPTION TAPE AND REEL Option 7	Option 9						
AGENCY CERTIFIED/PACKAGE	CTR (%)							
AGENOT GENTIFIED/FAGRAGE	10 mA							
UL, CSA, BSI	63 to 125 100 to 200							
DIP-6	SFH640-2 SFH640-3							
SMD-6, option 7	SFH640-2X007 SFH640-3X007T (1)						
VDE, UL, CSA, BSI	63 to 125 100 to 200							
SMD-6, option 9	- SFH640-3X019T (1)						

Notes

- Additional options may be possible, please contact sales office.
- (1) Also available in tubes, do not put T on the end.

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	VALUE UNIT					
INPUT								
Reverse voltage		V_{R}	6.0	V				
DC forward current		I _F	60	mA				
Surge forward current	t _p ≤ 10 µs	I _{FSM}	2.5	Α				
Total power dissipation		P _{diss}	100	mW				



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ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT					
OUTPUT									
Collector emitter voltage		V_{CEO}	300	V					
Collector base voltage		V_{CBO}	300	V					
Emitter base voltage		V_{EBO}	7.0	V					
Collector current		I _C	50	mA					
Surge collector current	$t_p \le 10 \text{ ms}$	I _C	100	mA					
Total power dissipation		P _{diss}	300	mW					
COUPLER									
Isolation test voltage		V_{ISO}	5300	V_{RMS}					
between emitter and detector		VISO	7500	V_{PK}					
Isolation resistance	$V_{IO} = 500 \text{ V}, T_{amb} = 25 ^{\circ}\text{C}$	R _{IO}	≥ 10 ¹²	Ω					
isolation resistance	V_{IO} = 500 V, T_{amb} = 100 °C	R _{IO}	≥ 10 ¹¹	Ω					
Insulation thickness between emitter and detector			≥ 0.4	mm					
Creepage distance			≥ 7	mm					
Clearance distance			≥ 7	mm					
Comparative tracking index per DIN IEC 112/VDE 0303, part 1		CTI	175						
Storage temperature range		T _{stg}	- 55 to + 150	°C					
Operating temperature range		T _{amb}	- 55 to + 100	°C					
Soldering temperature (1)	max. 10 s, dip soldering: distance to seating plane ≥ 1.5 mm	T _{sld}	260	°C					

Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.
- (1) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
	TEST CONDITION	FANI	STWIBOL	IVIIIV.	IIF.	IVIAA.	ONT
INPUT	T		T		1		
Forward voltage	I _F = 10 mA		V_V		1.1	1.5	V
Reverse voltage	$I_R = 10 \mu A$		V_R	6			V
Reverse current	V _R = 6 V		I _R		0.01	10	μA
Capacitance	V _F = 0 V, f = 1 MHz		Co		25		pF
Thermal resistance			R _{thja}		750		K/W
OUTPUT							
Collector emitter breakdown voltage	$I_{CE} = 1 \text{ mA},$ $R_{BE} = 1 \text{ M}\Omega$		BV _{CER}	300			V
Voltage emitter base	I _{EB} = 10 μA		BV _{BEO}	7			V
Collector emitter capacitance	V _{CE} = 10 V, f = 1 MHz		C _{CE}		7		pF
Collector base capacitance	V _{CB} = 10 V, f = 1 MHz		C _{CB}		8		pF
Emitter base capacitance	V _{EB} = 5 V, f = 1 MHz		C _{EB}		38		pF
Thermal resistance			R _{thja}		250		K/W
COUPLER							
Coupling capacitance			C _C		0.6		pF
Saturation voltage collector	$I_F = 10 \text{ mA}, I_C = 3.2 \text{ mA}$	SFH640-2	V _{CEsat}		0.25	0.4	V
emitter	$I_F = 10 \text{ mA}, I_C = 5 \text{ mA}$	SFH640-3	V _{CEsat}		0.25	0.4	V
Collector emitter leakage current	$V_{CE} = 200 \text{ V}, R_{BE} = 1 \text{ M}\Omega$		I _{CER}		1	100	nA

Note

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering
evaluation. Typical values are for information only and are not part of the testing requirements.



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CURRENT TRANSFER RATIO (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Current transfer ratio	$I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V}$	SFH640-2	I _C /I _F	63		125	%
	I _F = 1 mA, V _{CE} = 10 V	SFH640-2	I _C /I _F	22	45		%
	$I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V}$	SFH640-3	I_{C}/I_{F}	100		200	%
	$I_F = 1 \text{ mA}, V_{CE} = 10 \text{ V}$	SFH640-3	I _C /I _F	34	70		%

SWITCHING CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Turn-on time	$I_C = 2 \text{ mA}, R_L = 100 \Omega, V_{CC} = 10 \text{ V}$	t _{on}		5		μs
Rise time	I_C = 2 mA, R_L = 100 Ω , V_{CC} = 10 V	t _r		2.5		μs
Turn-off time	$I_C = 2 \text{ mA}, R_L = 100 \Omega, V_{CC} = 10 \text{ V}$	t _{off}		6		μs
Fall time	$I_C = 2 \text{ mA}, R_L = 100 \Omega, V_{CC} = 10 \text{ V}$	t _f		5.5		μs

TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

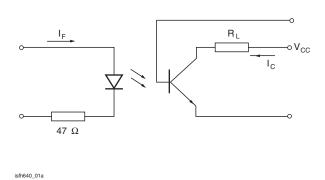


Fig. 1 - Switching Times Measurement Test Circuit and Waveform

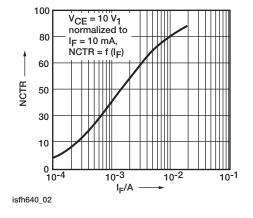


Fig. 3 - Current Transfer Ratio (typ.)

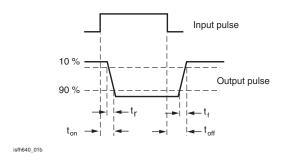


Fig. 2 - Switching Times Measurement Test Circuit and Waveform

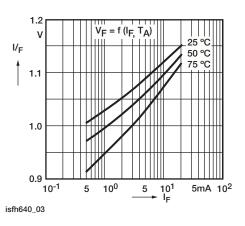


Fig. 4 - Diode Forward Voltage (typ.)



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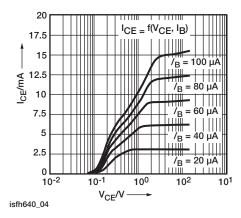


Fig. 5 - Output Characteristics (typ.)

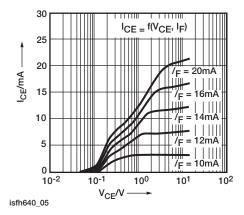


Fig. 6 - Output Characteristics (typ.)

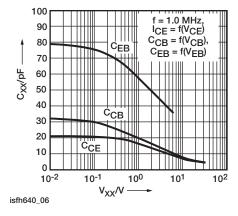


Fig. 7 - Transistor Capacitances (typ.)

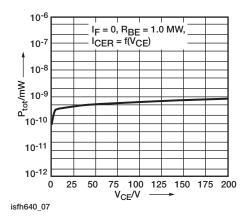


Fig. 8 - Collector-Emitter Leakage Current (typ.)

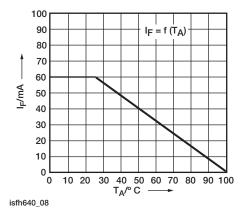


Fig. 9 - Permissible Loss Diode

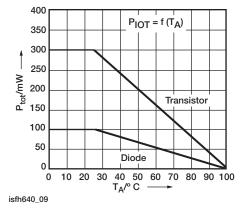
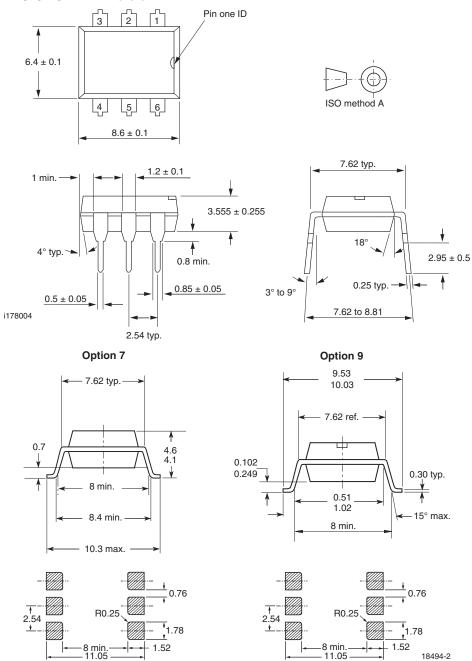


Fig. 10 - Permissible Power Dissipation

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PACKAGE DIMENSIONS in millimeters

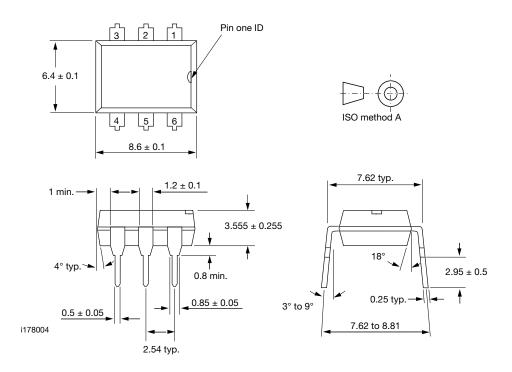






DIP-6A

PACKAGE DIMENSIONS in inches (millimeters)



Note

The information in this document provides generic information but for specific information on a product the appropriate product datasheet should be used.



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